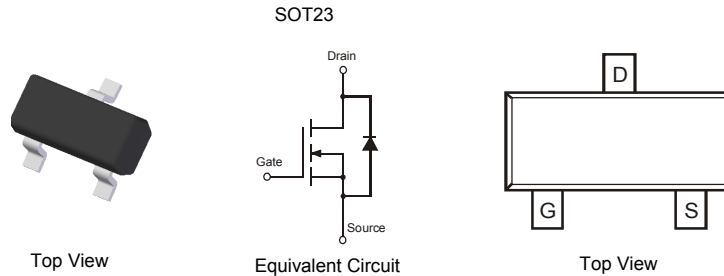


## Features

- Low On-Resistance
  - 29mΩ @ V<sub>GS</sub> = 4.5V
  - 50mΩ @ V<sub>GS</sub> = 2.5V
  - 100mΩ @ V<sub>GS</sub> = 2.0V
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 **(e3)**
- Weight: 0.008 grams (approximate)

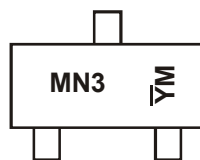


## Ordering Information (Note 4)

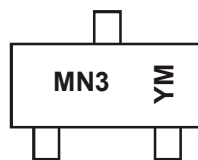
Part Number	Case	Packaging
DMN2050L-7	SOT23	3000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  - See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



Chengdu A/T Site



Shanghai A/T Site

MN3 = Marking Code  
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)  
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)  
 Y or Y = Year (ex: A = 2013)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	I <sub>D</sub>	5.9	A
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	21	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.45	—	1.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	24	29	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.0A
			42	50		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.1A
			68	100		V <sub>GS</sub> = 2.0V, I <sub>D</sub> = 1.5A
Forward Transfer Admittance	Y <sub>fs</sub>	—	8	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 2.1A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	0.9	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.0A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	532	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	144	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	117	—	pF	
Gate Resistance	R <sub>G</sub>	—	1.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Total Gate Charge	Q <sub>g</sub>	—	6.7	—	nC	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.0A
Gate-Source Charge	Q <sub>gs</sub>	—	0.8	—		V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.0A
Gate-Drain Charge	Q <sub>gd</sub>	—	3.0	—		V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5.0A

- Notes:
5. Device mounted on FR-4 PCB, on 2oz Copper pad layout with R<sub>θJA</sub> = 90°C/W.
  6. Repetitive rating, pulse width limited by junction temperature.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to production testing.

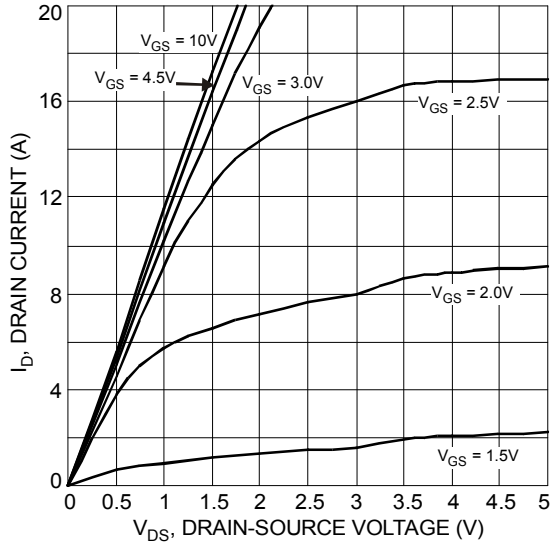


Fig. 1 Typical Output Characteristic

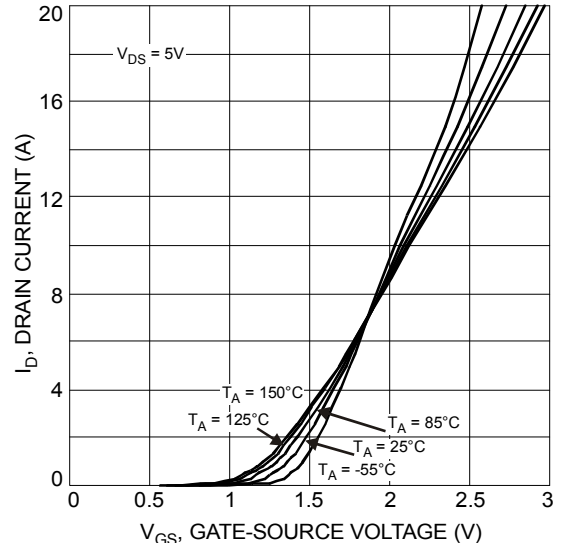


Fig. 2 Typical Transfer Characteristic

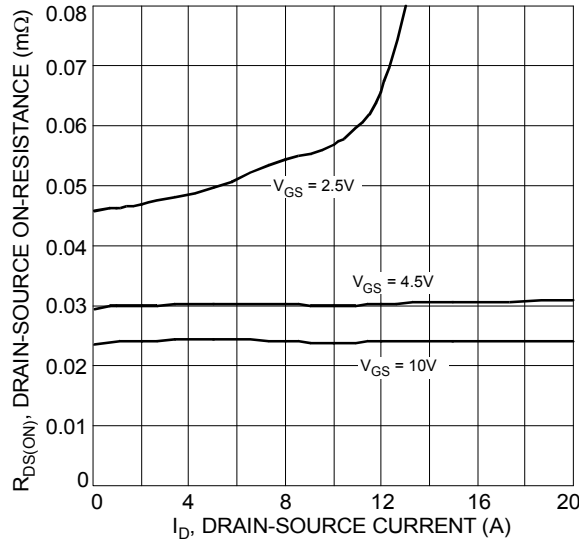


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

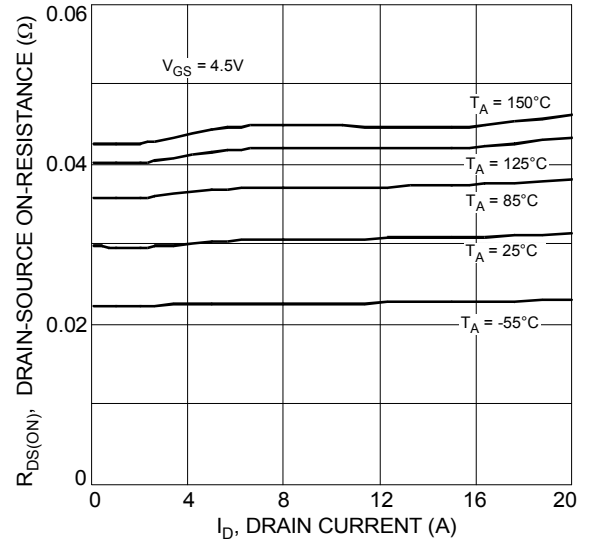


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

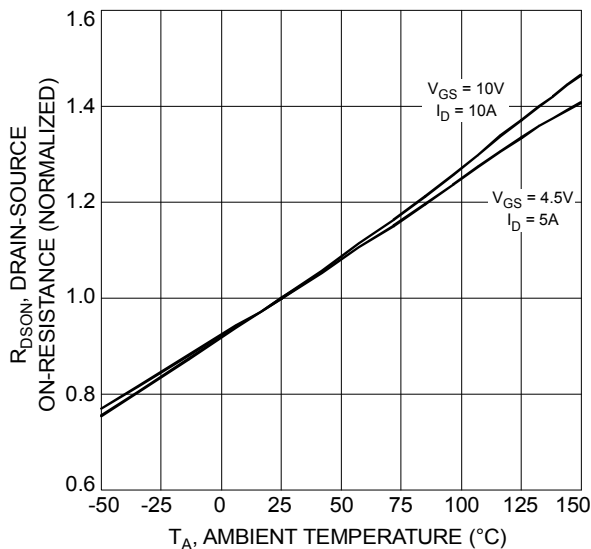


Fig. 5 On-Resistance Variation with Temperature

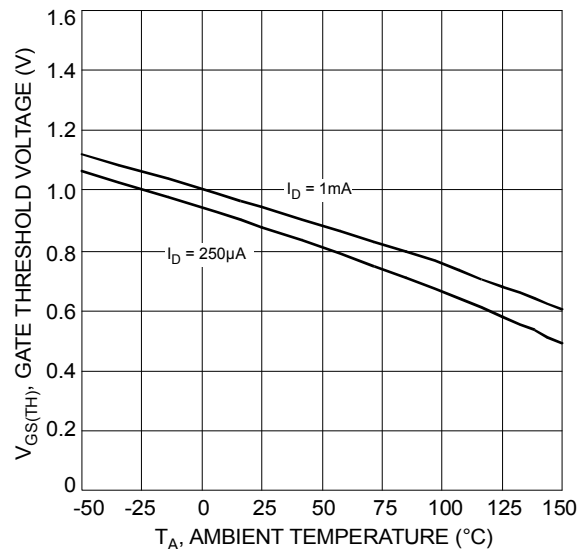


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

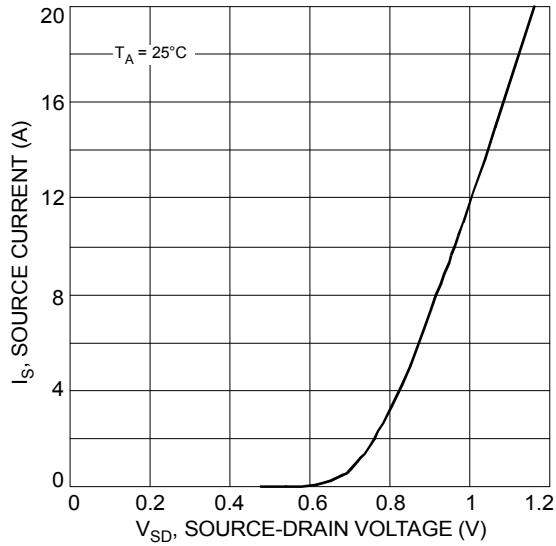


Fig. 7 Diode Forward Voltage vs. Current

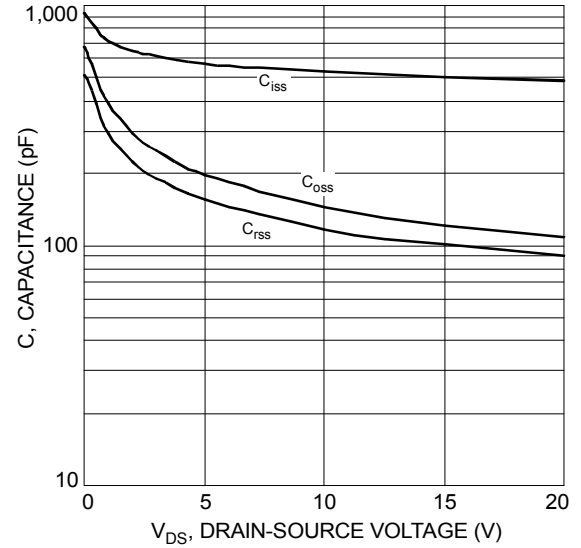


Fig. 8 Typical Total Capacitance

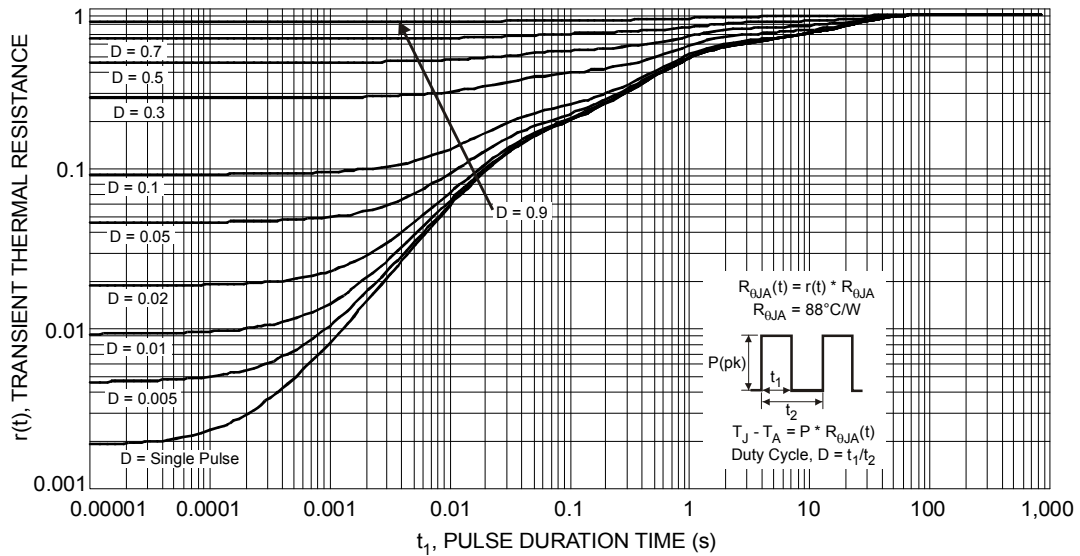
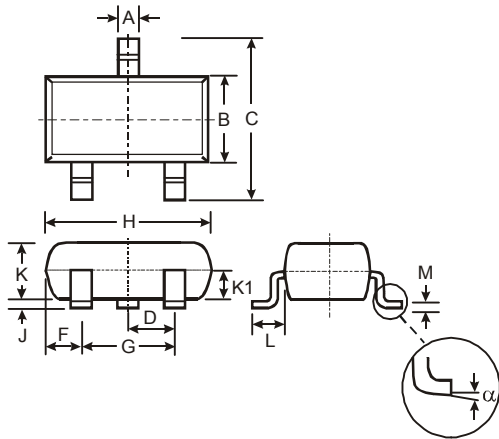


Fig. 9 Transient Thermal Response

# Package Outline Dimensions

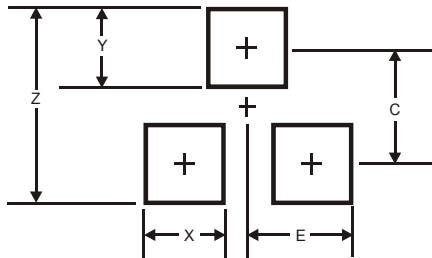
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

# Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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